IN THE CLAIMS:

Claims 1-7 (Canceled).

8. (Currently Amended) A method of making a solder ball, the method comprising the steps of:

preparing a spherical core;

forming a plating layer, including Sn and Ag, by an electroplating technique such that the plating layer wraps the core up;

heating the core with the plating layer, thereby keeping the plating layer molten for a predetermined period of time; and

solidifying the molten plating layer, thereby making a solder layer,

wherein the step of forming the plating layer includes the step of forming an alloy plating layer including Sn and Ag and wherein the step of forming the plating layer includes the step of forming an additional plating layer including Ag.

Claims 9-10 (Canceled).

11. (Original) The method of claim 8, wherein the step of forming the plating layer includes the steps of:

forming a first plating layer, including Sn, such that the first plating layer wraps the core up, and

forming a second plating layer, including Ag, such that the second plating layer also wraps the core up.

12. (Previously Presented) The method of claim 8, wherein the solder layer includes Cu, Sn and Ag.

13. (Original) The method of claim 12, wherein the solder layer includes 0.5 mass % to 4.0 mass % of Ag.

14. (Original) The method of claim 12, wherein the solder layer includes 3.5 mass % of Ag.

15. (Canceled)

16. (Original) A method of making a solder ball, the method comprising the steps of

preparing a spherical core, and

forming a solder layer, including Sn and Ag, such that the solder layer wraps the core up,

wherein the step of forming the solder layer includes the step of forming a first solder layer, including an Sn--Ag alloy, by an electroplating process that uses a plating solution including 10 g/l to 25 g/l of tris (3-hydroxypropyl) phosphine, 15 g/l to 25 g/l of Sn organosulfonate, 0.3 g/l to 1.5 g/l of Ag organosulfonate, 50 g/l to 100 g/l of organic sulfonic acid, and ammonia, and

wherein the first solder layer includes 0.5 mass % to 2.5 mass % of Ag.

17. (Original) The method of claim 16, wherein the plating solution further includes 3 g/l to 12 g/l of thiourea.

18. (Previously Presented) The method of claim 16, wherein the step of forming the solder layer further includes the step of forming a second solder layer including Ag.

19. (Original) The method of claim 18, wherein the second solder layer is formed by an electroplating process, an evaporation process or a colloidal process.

20. (Original) The method of claim 19, wherein the second solder layer is formed by the electroplating process and has a thickness of at most 0.5 μm.

21. (Previously Presented) The method of claim 18, wherein the solder layer includes 3.0 mass % to 4.0 mass % of Ag.

22. (Previously Presented) The method of claim 16, wherein the first solder layer has a thickness of 3 μm to 50 μm.

23. (Previously Presented) The method of claim 16, wherein the core is made of Cu, Al or a resin.

24. (Previously Presented) The method of claim 16, wherein the solder layer includes 3.5 mass % of Ag.

25. (Previously Presented) The method of claim 16, wherein the core has a diameter of 0.05 mm to 1 mm.

Claims 26-27 (Canceled).

28. (Currently Amended) A solder ball comprising

a spherical core, and

a solder layer, which includes Sn and Ag and which is provided so as to wrap the core up,

wherein the solder layer includes a first solder layer made of an Sn--Ag alloy, and

wherein the first solder layer includes 0.5 mass % to 2.5 mass % of Ag, and

wherein ~~the~~ an amount of water contained in the solder layer is 100 μl/g or less when represented by ~~the~~ an amount of water vapor in standard conditions,

wherein the solder layer further includes a second solder layer, which is provided so as to wrap up the first solder layer, and wherein the second solder layer includes Ag and has a thickness of at most 0.5 μm.

29. (Canceled)

30. (Currently Amended) The solder ball of claim ~~29~~ 28, wherein the solder layer includes 3.0 mass % to 4.0 mass % of Ag.

31. (Previously Presented) The solder ball of claim 28, wherein the first solder layer has a thickness of 3 μm to 50 μm.

32. (Previously Presented) The solder ball of claim 28, wherein the core is made of Cu, Al or a resin.

33. (Previously Presented) The solder ball of claim 30, wherein the solder layer includes 3.5 mass % of Ag.

34. (Previously Presented) The solder ball of claim 28, wherein the core has a diameter of 0.05 mm to 1 mm.

35. (Canceled)